TetraFET

D2006UK

METAL GATE RF SILICON FET

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 15W – 28V – 1GHz PUSH–PULL

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 13 dB MINIMUM

APPLICATIONS

• HF/VHF/UHF COMMUNICATIONS from DC to 2 GHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

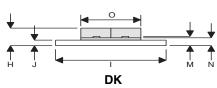
P _D	Power Dissipation	70W
BV _{DSS}	Drain – Source Breakdown Voltage *	65V
BV _{GSS}	Gate – Source Breakdown Voltage *	±20V
I _{D(sat)}	Drain Current *	3A
T _{stg}	Storage Temperature	–65 to 150°C
Тj	Maximum Operating Junction Temperature	200°C

* Per Side

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MECHANICAL DATA



PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	GATE 2

PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
Α	6.45	0.13	0.254	0.005
В	1.65R	0.13	0.065R	0.005
С	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
н	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
М	0.13	0.02	0.005	0.001
Ν	2.16	0.13	0.085	0.005



ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit	
	PER SIDE							
BV _{DSS}	Drain-Source	$V_{GS} = 0$	I _D = 10mA	65			V	
	Breakdown Voltage			05			v	
IDSS	Zero Gate Voltage	V _{DS} = 28V	V _{GS} = 0			3	mA	
	Drain Current					3	IIIA	
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	$V_{DS} = 0$			1	μA	
V _{GS(th)}	Gate Threshold Voltage *	I _D = 10mA	$V_{DS} = V_{GS}$	1		7	V	
9 _{fs}	Forward Transconductance *	V _{DS} = 10V	I _D = 0.6A	0.54			S	
		тот	AL DEVICE					
G _{PS}	Common Source Power Gain	P _O = 15W		13			dB	
η	Drain Efficiency	V _{DS} = 28V	I _{DQ} = 0.6A	40			%	
VSWR	Load Mismatch Tolerance	f = 1GHz		20:1			—	
PER SIDE								
C _{iss}	Input Capacitance	$V_{DS} = 0$	$V_{GS} = -5V f = 1MHz$			36	pF	
C _{oss}	Output Capacitance	V _{DS} = 28V	$V_{GS} = 0$ f = 1MHz			18	pF	
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 28V$	$V_{GS} = 0$ f = 1MHz			1.5	pF	

* Pulse Test: Pulse Duration = 300 μ s , Duty Cycle \leq 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 2.5°C / W
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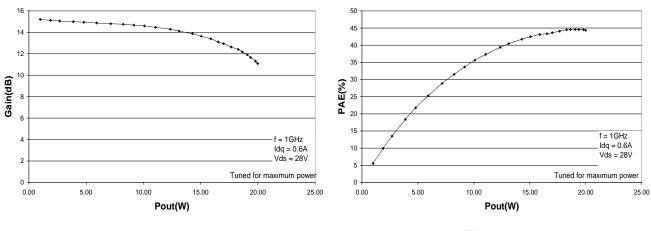
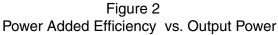


Figure 1 Gain vs. Output Power



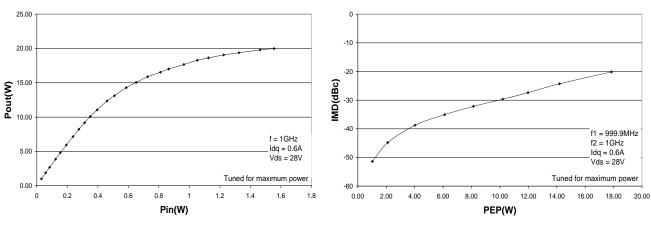
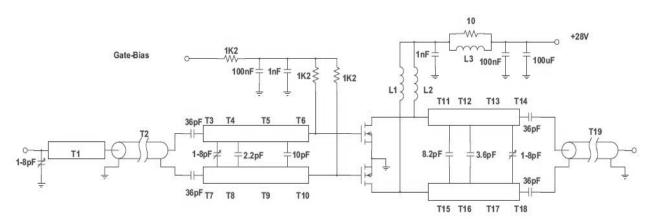


Figure 3 Output Power vs. Input Power Figure 4 IMD3 vs. PEP

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1000MHz TEST FIXTURE

Substrate 0.8mm thick PTFE/glass All microstrip lines W = 2.7mm

- T1 23 mm
- T2, T19 50mm 50 OHM UT 34 semi-rigid coax
- T3, T7 6mm
- T4, T8 8mm
- T5, T9 15mm
- T6, T10 9mm
- T11,T15 8mm
- T12,T16 7mm
- T13,T17 11mm
- T14,T18 5mm
- L1,L2 6 turns of 24swg enamelled copper wire, 3mm i.d.
- L3 1.5 turns of 24swg enamelled copper wire on Siemens B62152-a7x 2 hole core

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